

Power MOSFET and Schottky Diode -20 V, -4.1 A, P-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm, uCool Package, MOSFET PFET 2X2 20V 4.1A 106MOHM

Manufacturers	ON Semiconductor, LLC
Package/Case	WDFN-6
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for NTLJF3117PT1G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Power MOSFET and Schottky Diode-20 V, -4.1 A, P-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm, uCool™ Package

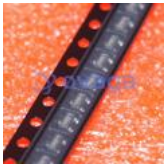
Features

- FETKY™ Configuration with MOSFET plus Low Vf Schottky Diode
- uCool™ Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- 2x2 mm Footprint Same as SC-88 Package Design
- Independent Pinout Provides Circuit Design Flexibility
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environment
- High Current Schottky Diode: 2 A Current Rating
- This is a Pb-Free Device

Application

ONSEMI

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